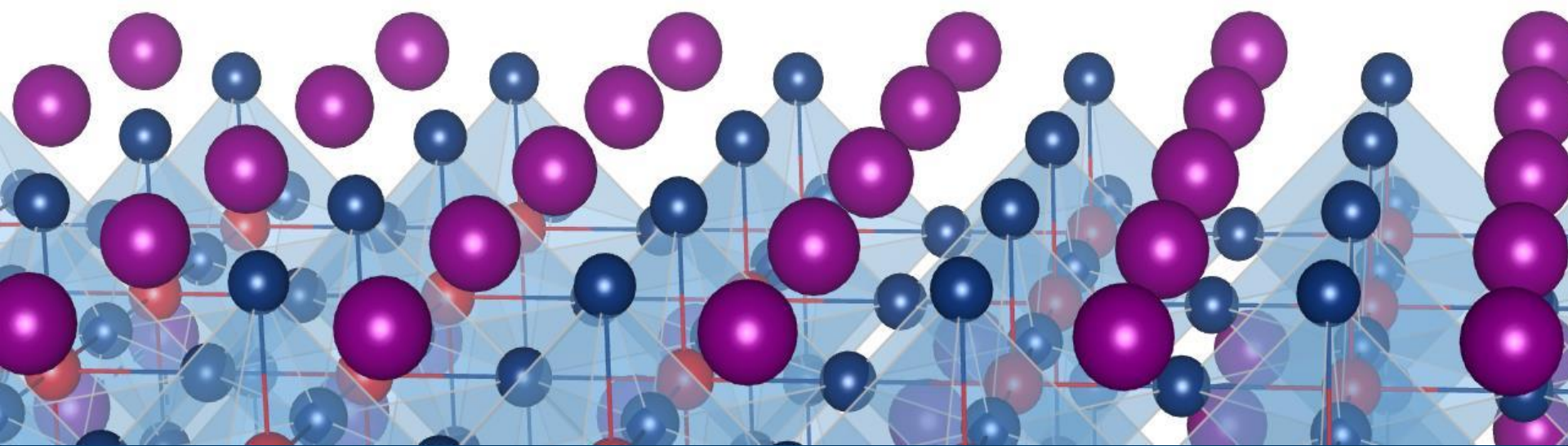


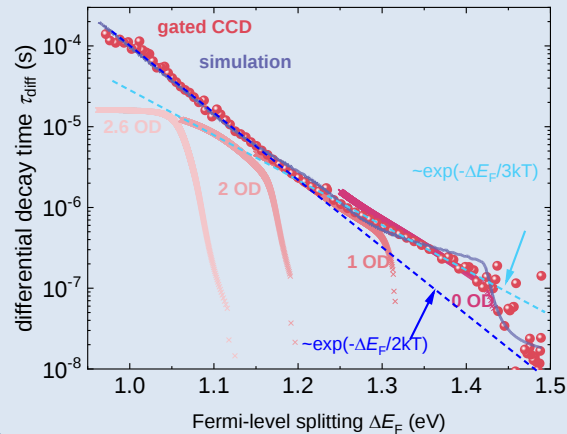


SHALLOW DEFECTS AND LONG CHARGE-CARRIER LIFETIMES IN LEAD-HALIDE PEROVSKITES

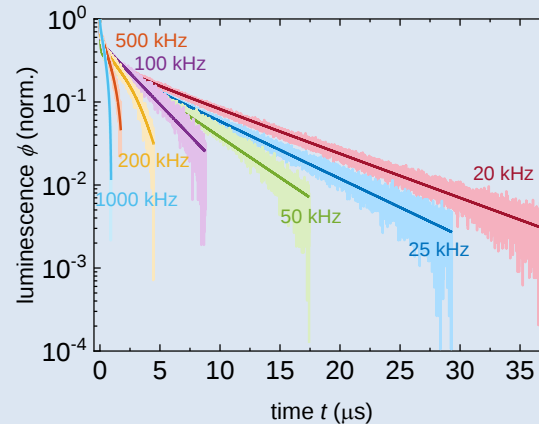
Thomas Kirchartz, Lisa Krückemeier, Genghua Yan, Ye Yuan, Uwe Rau

IEK-5 Photovoltaik, Forschungszentrum Jülich

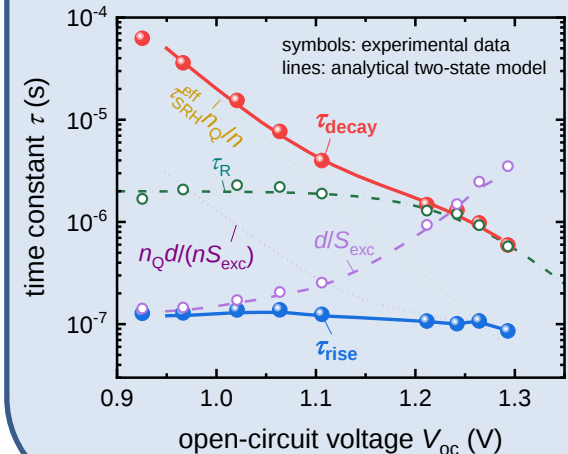
1) On the importance of shallow defects

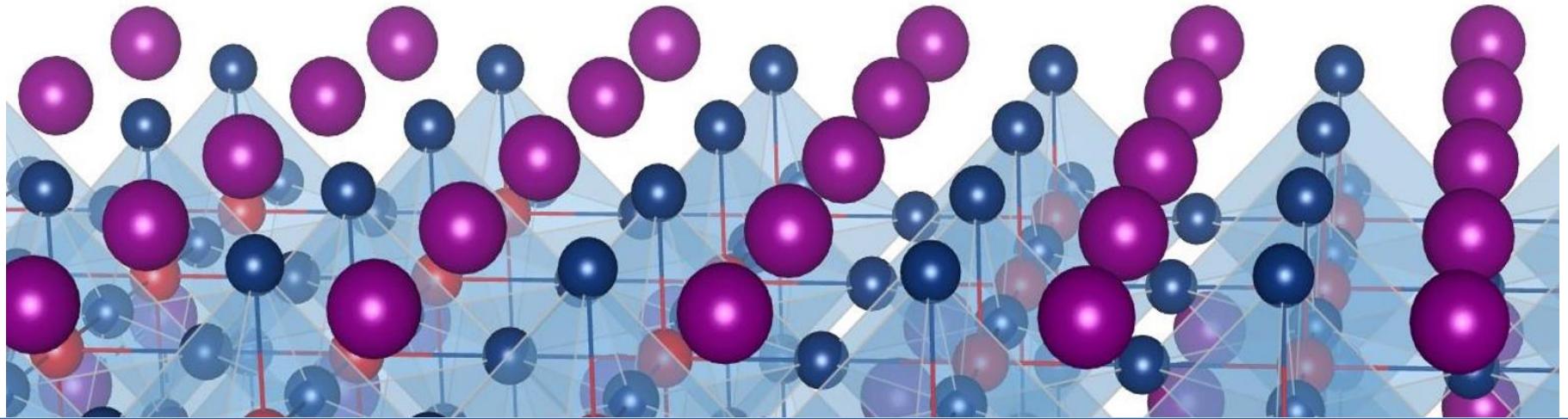


2) On the importance of repetition rates



3) Matrix models (for fans of linear algebra)





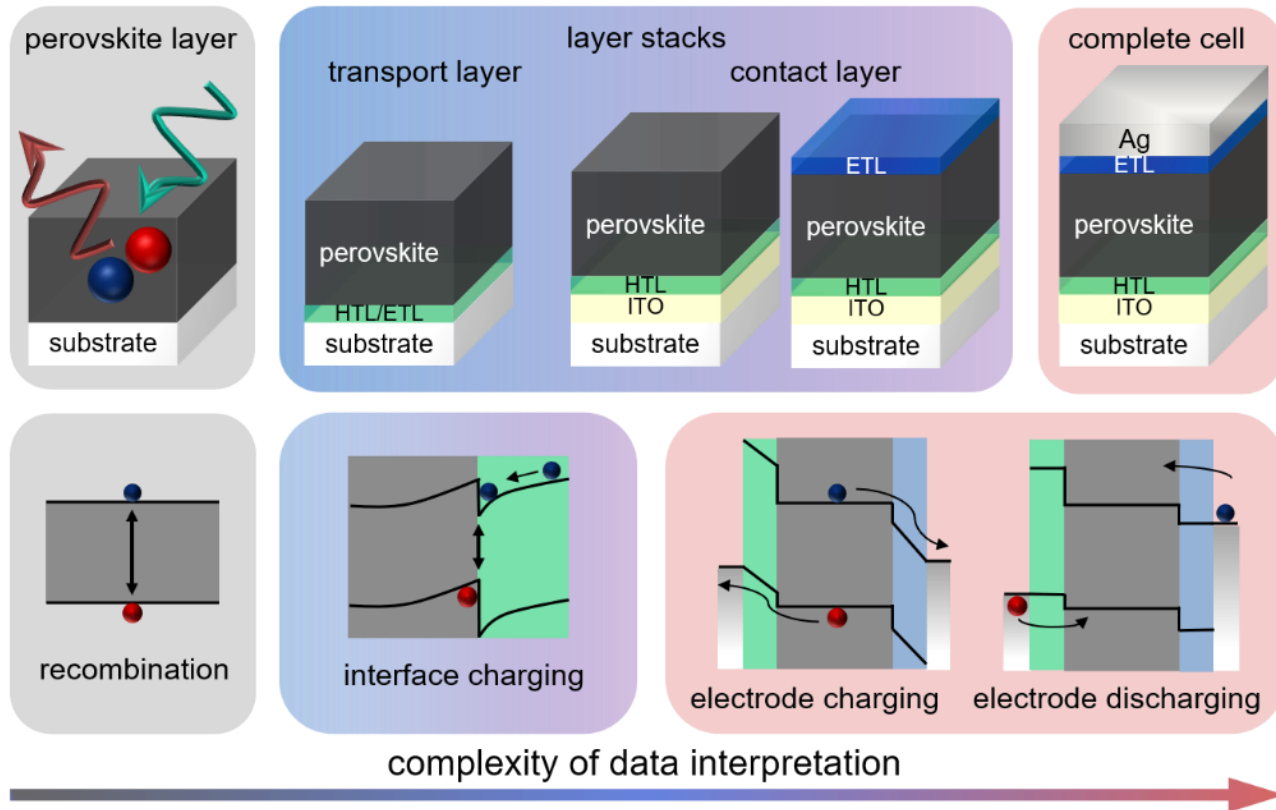
PART 0: INTRODUCTION

TRANSIENT PHOTOLUMINESCENCE AND LIFETIMES

Transient Photoluminescence in Lead-Halide Perovskite Layer Stacks and Solar Cells

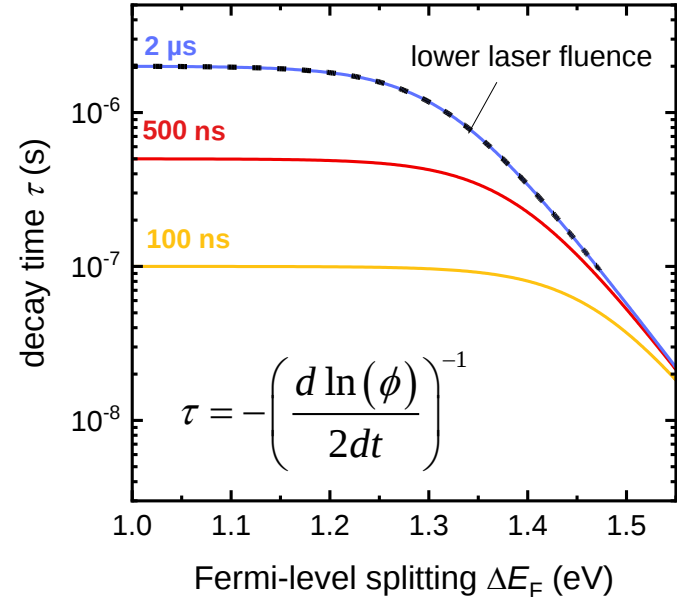
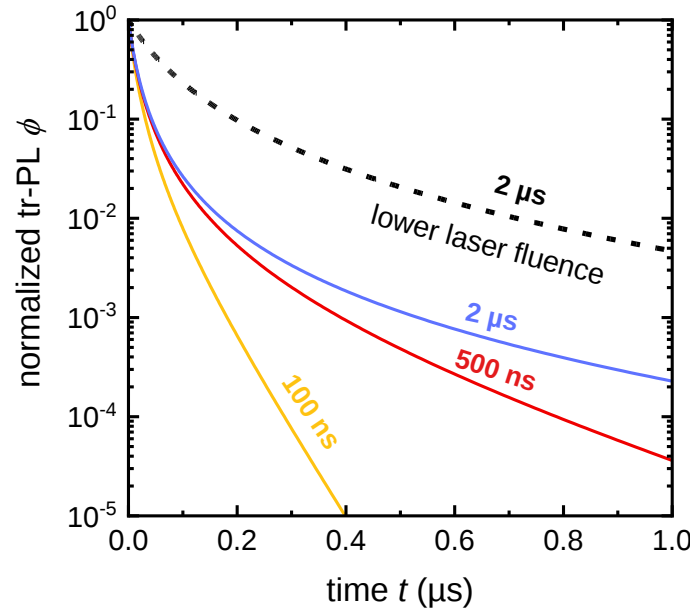
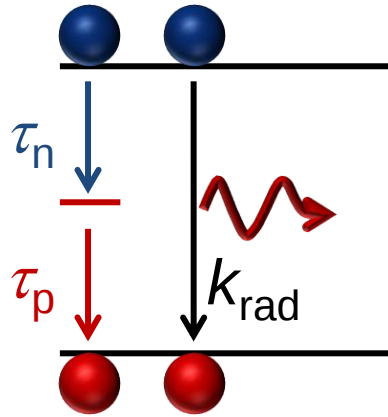
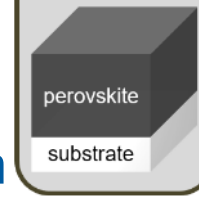
$$\phi_{\text{PL}} \propto np \approx n^2$$

Our samples are intrinsic (i.e. have a very low dark carrier concentration)



Transient Photoluminescence

Layer on Glass – Bulk Recombination



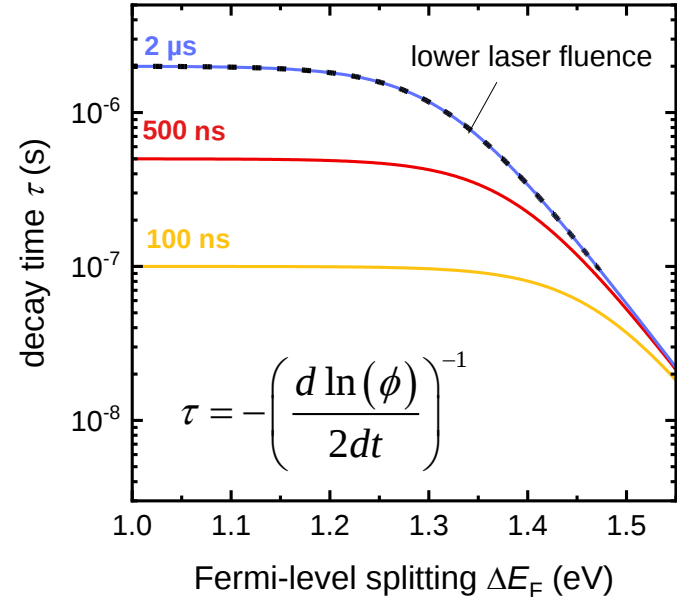
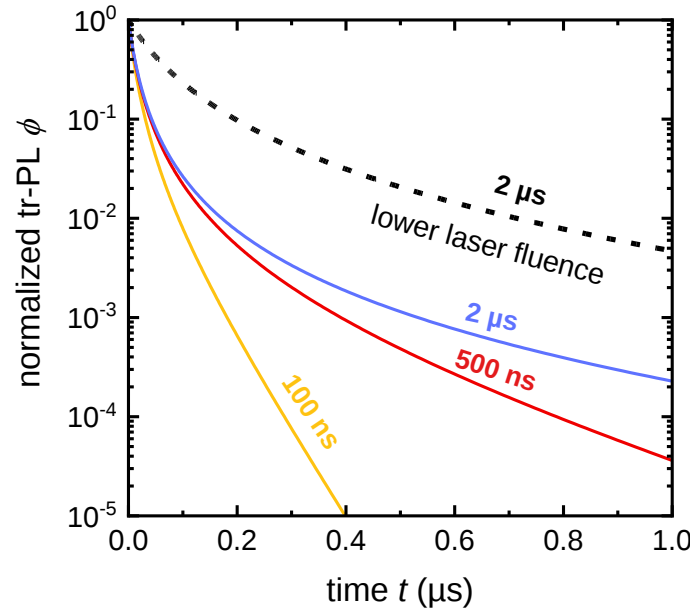
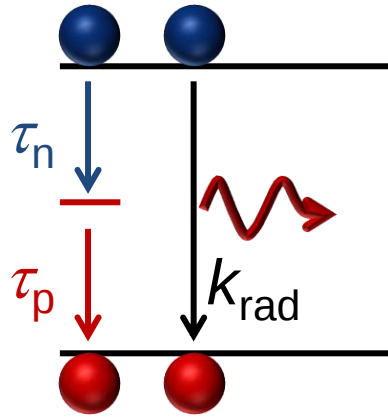
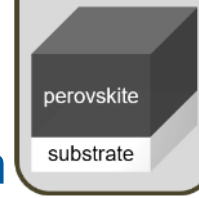
$$\frac{dn}{dt} = -k_{\text{rad}} n^2 - \frac{n}{\tau_p + \tau_n}$$

SRH + radiative recombination

← time

Transient Photoluminescence

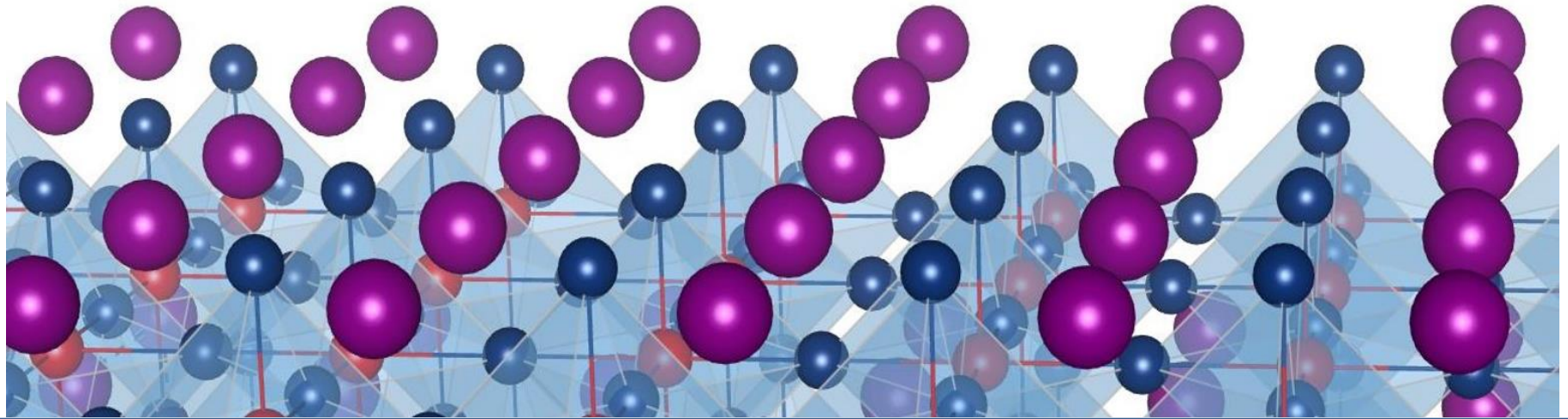
Layer on Glass – Bulk Recombination



$$\tau_{\text{diff}} = -\frac{n}{dn/dt} = \frac{1}{k_{\text{rad}}n + \tau_p + \tau_n}$$

Decay Time

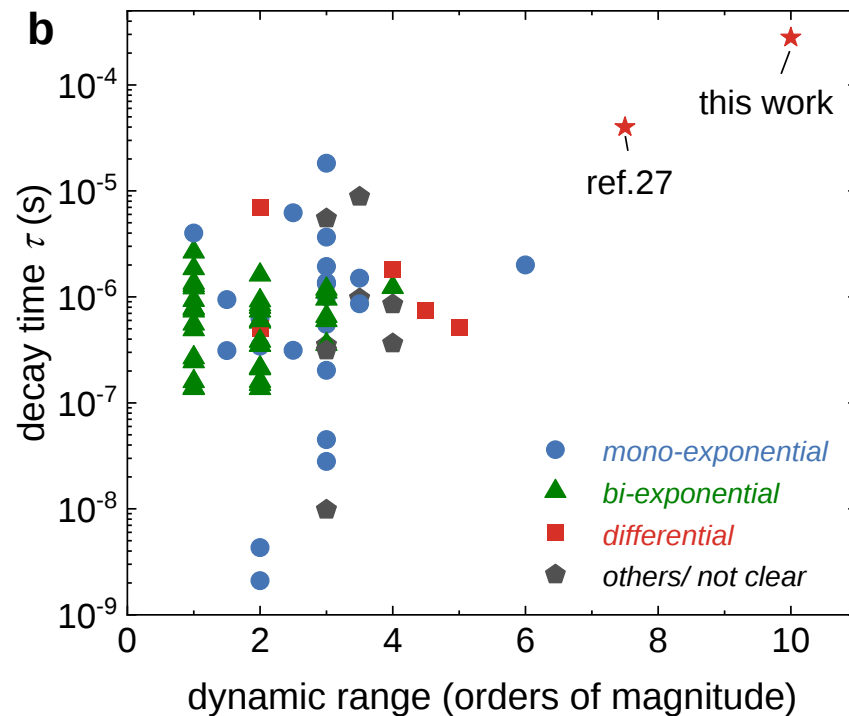
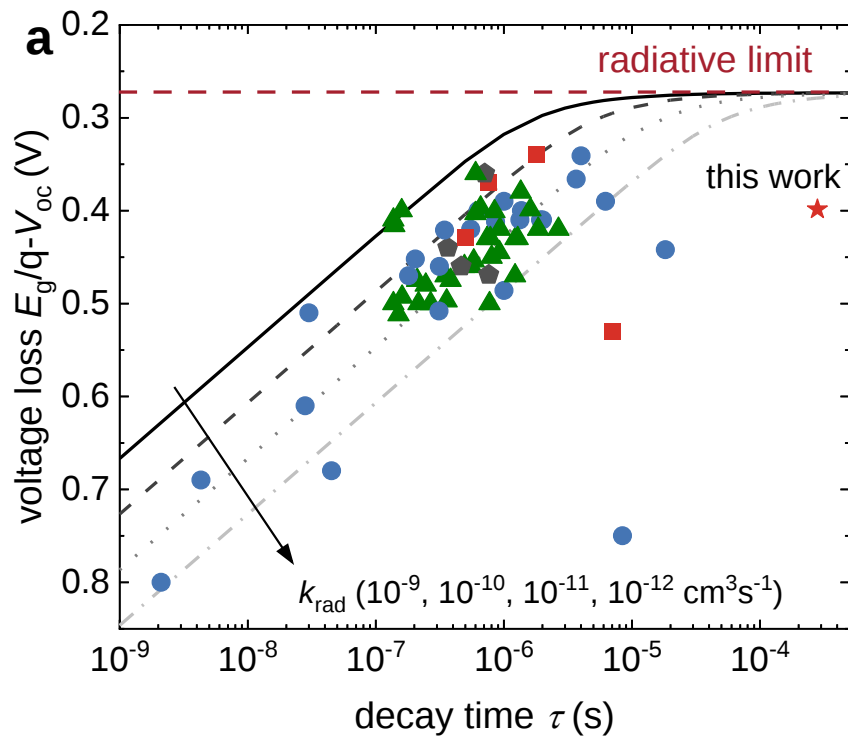
← time



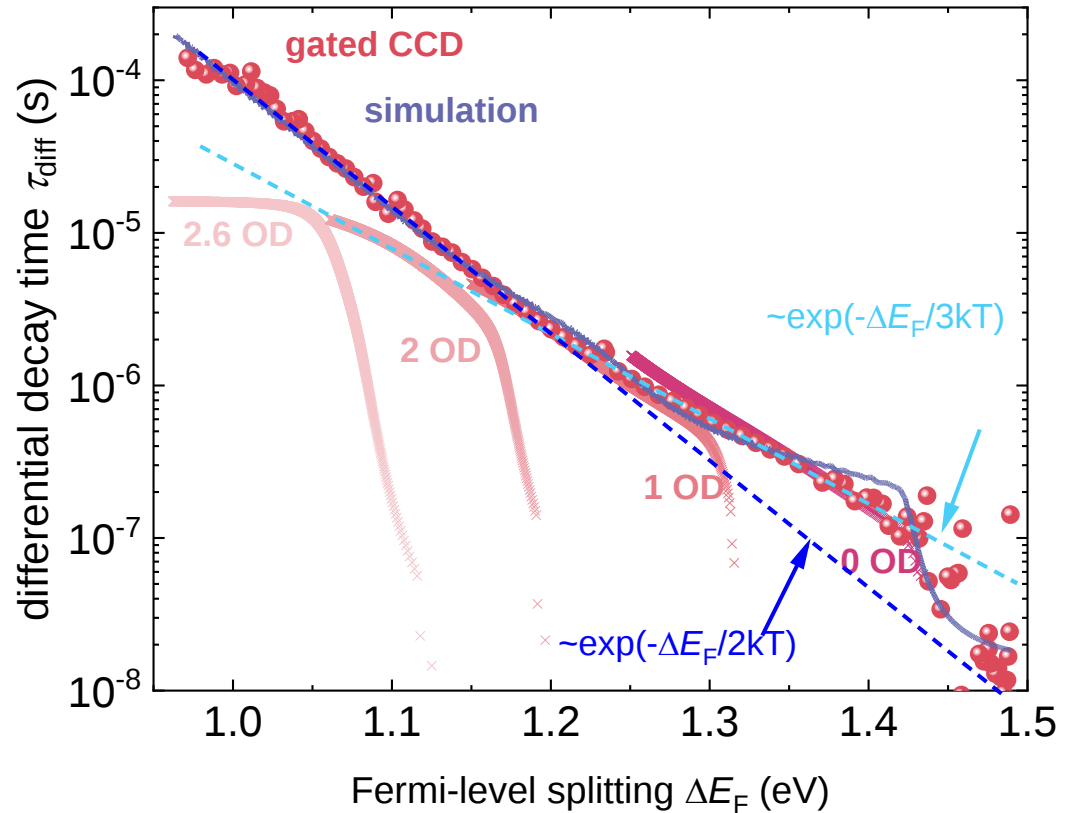
PART 1: SHALLOW DEFECTS

AND HOW THEY CHANGE THE SITUATION

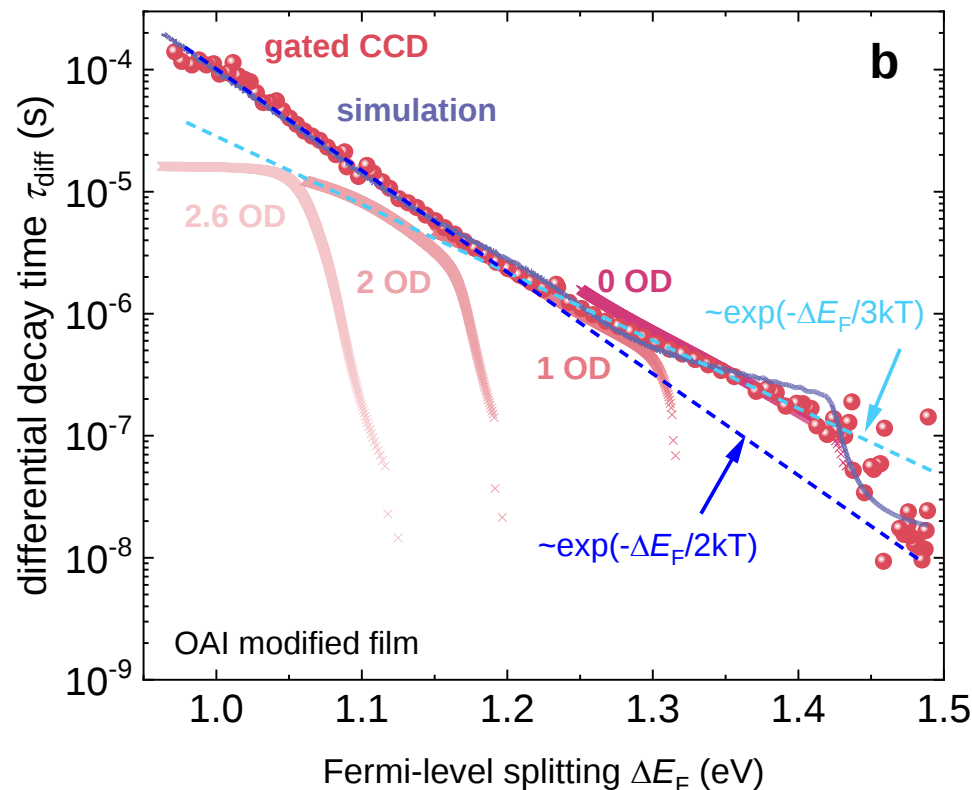
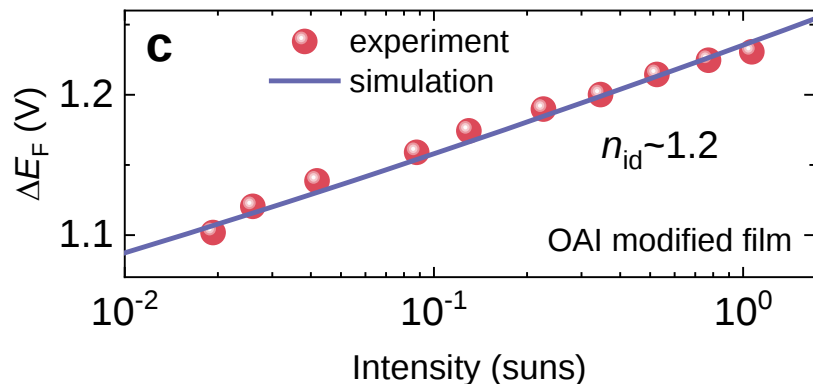
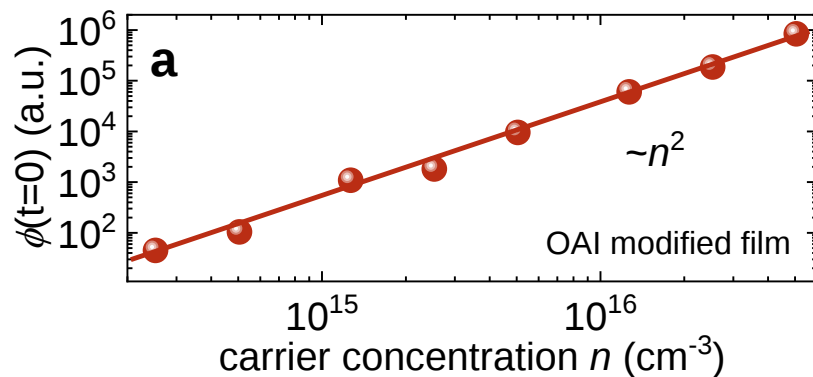
The importance of dynamic range



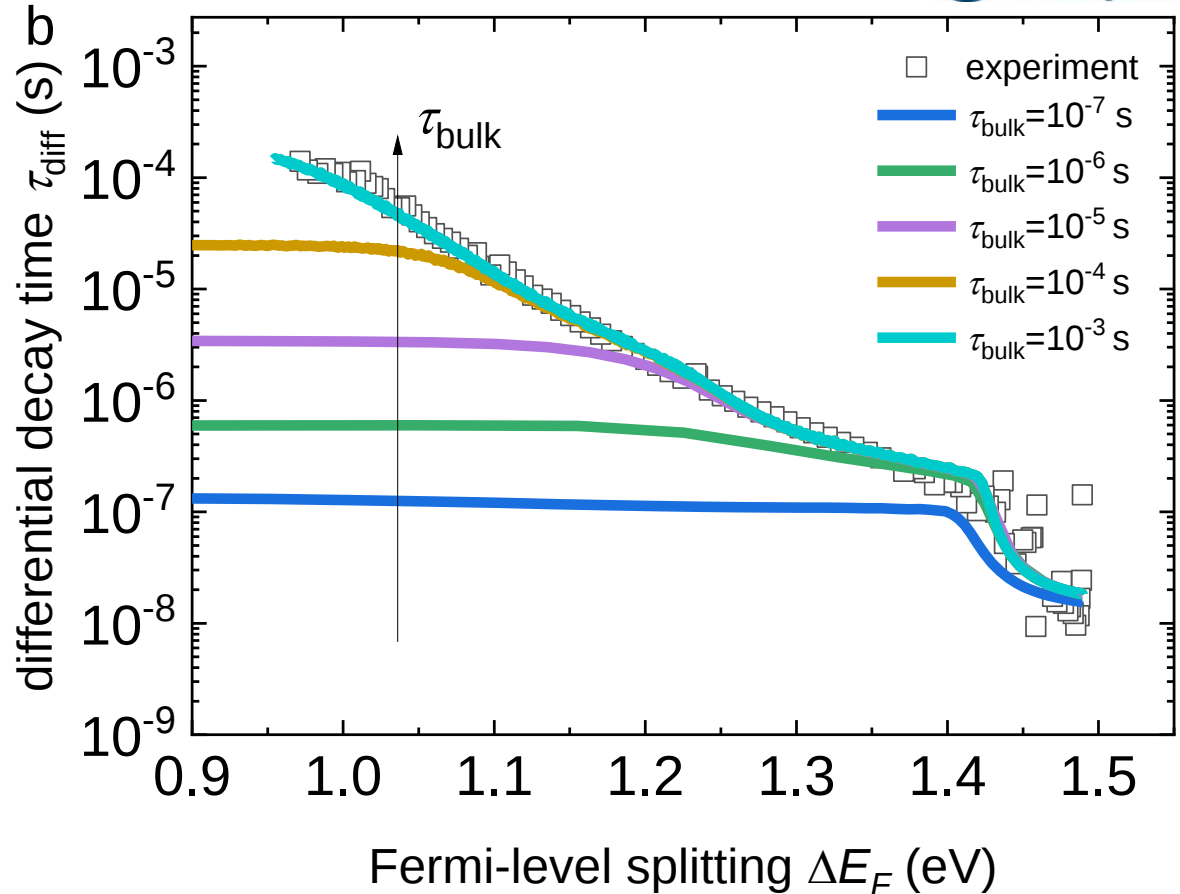
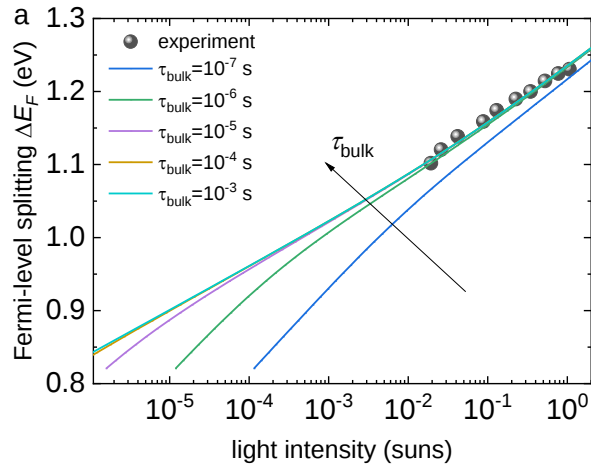
Steady state vs. tr-PL



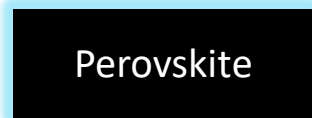
Steady state vs. tr-PL



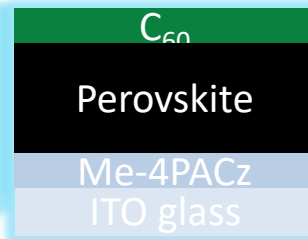
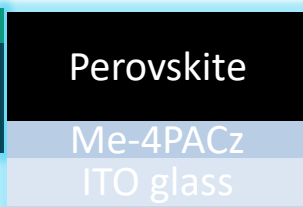
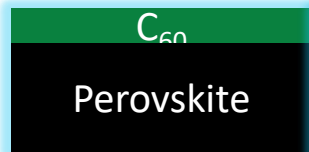
On the presence or absence of deep defects



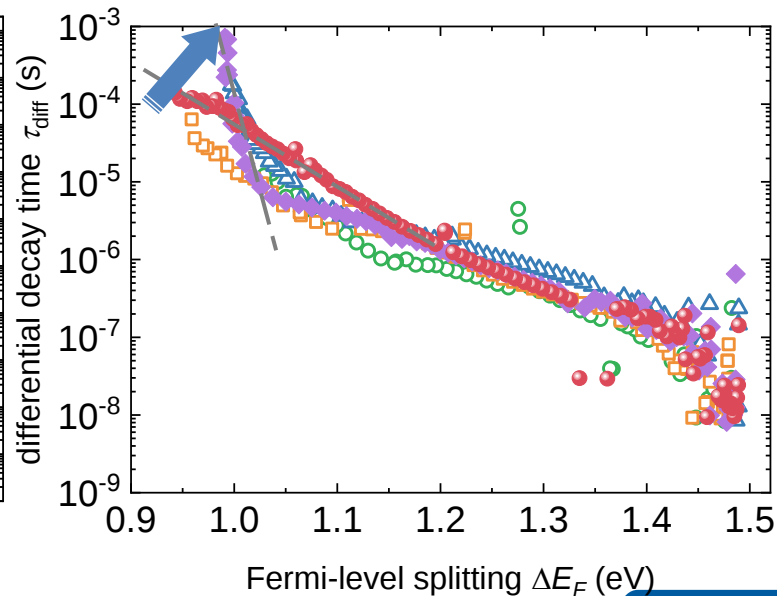
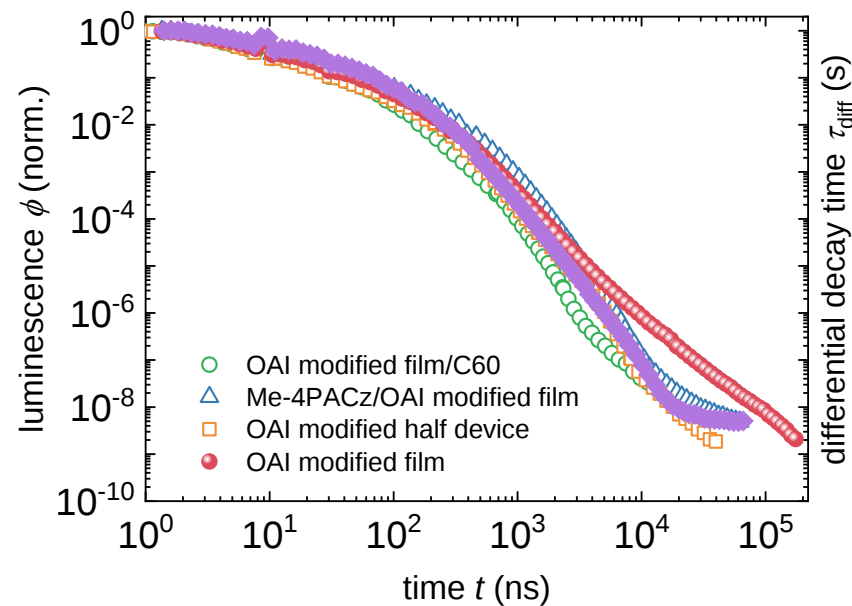
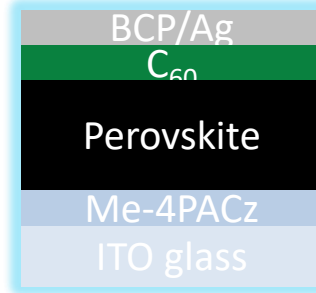
Pure film



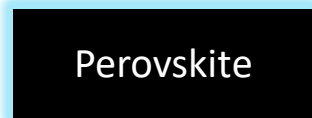
stacks



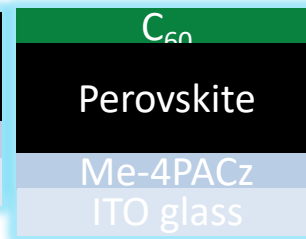
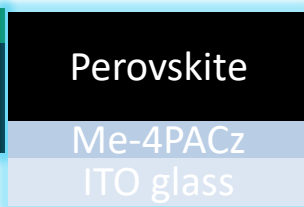
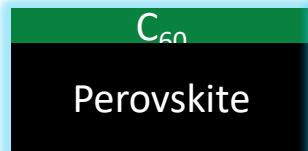
full device



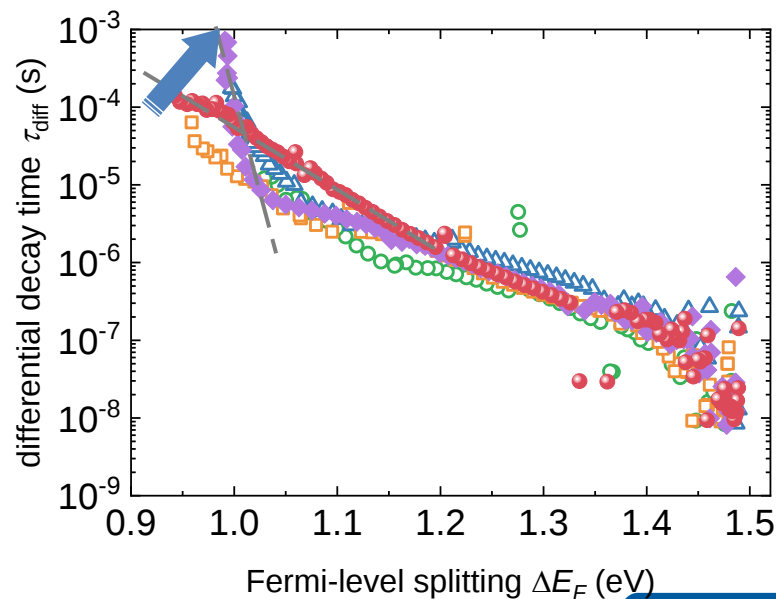
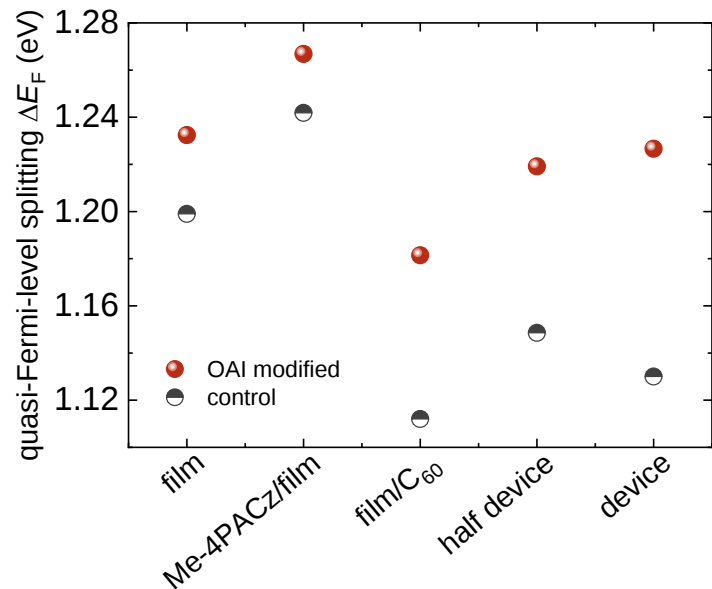
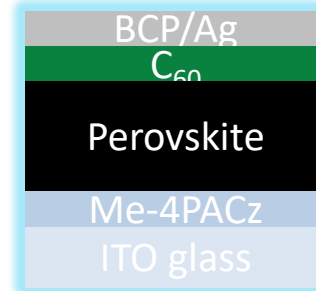
Pure film



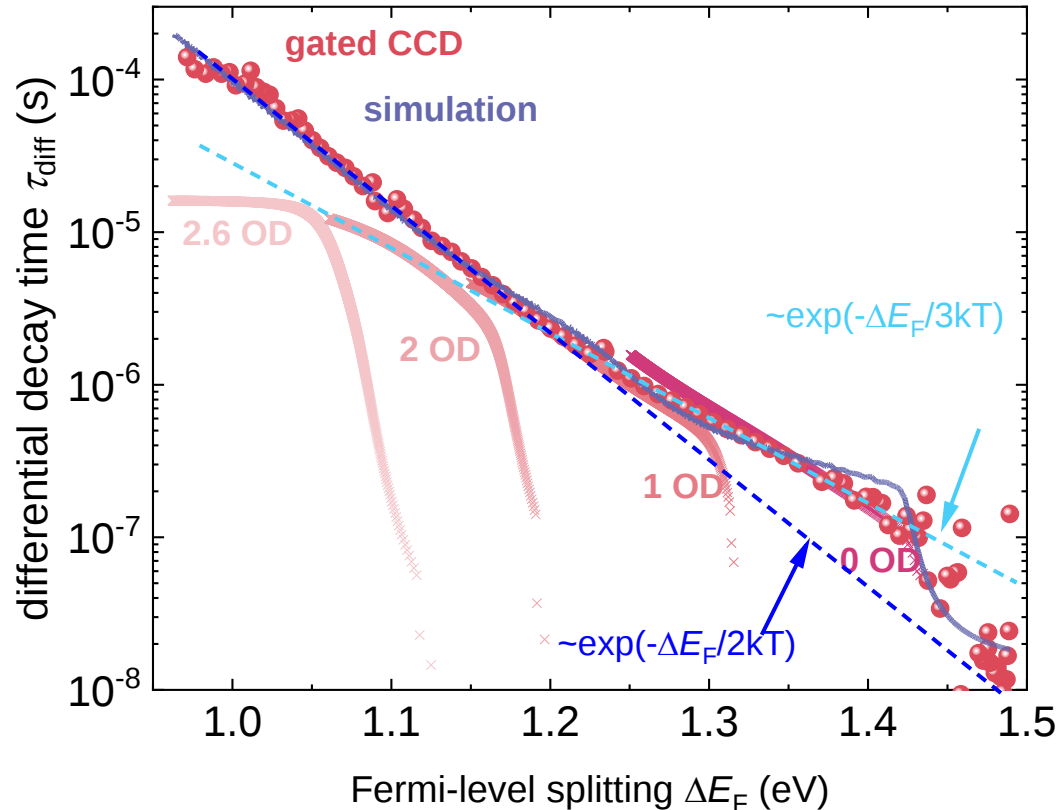
stacks



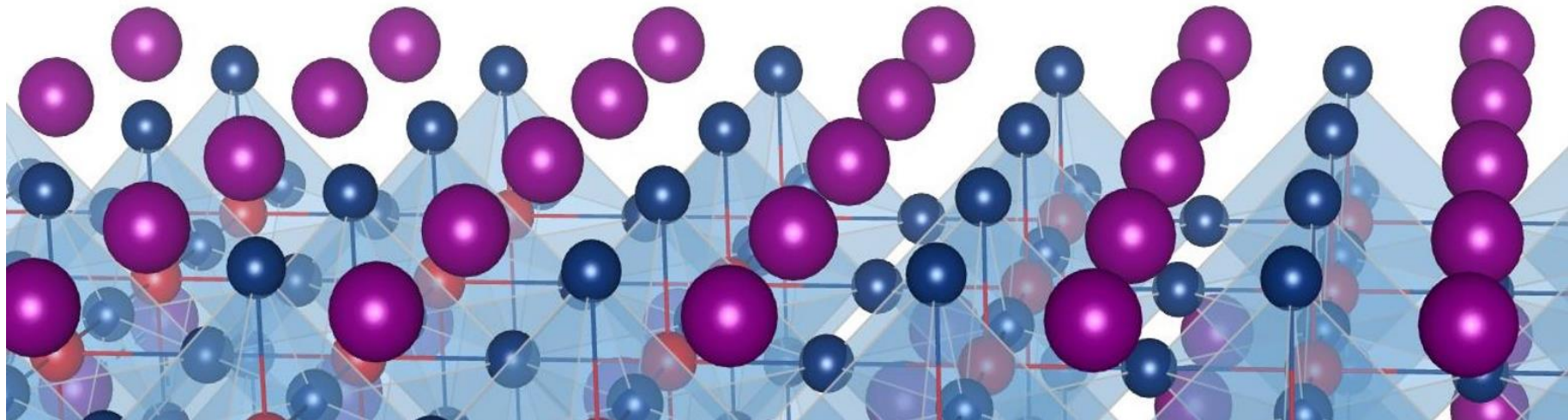
full device



Summary

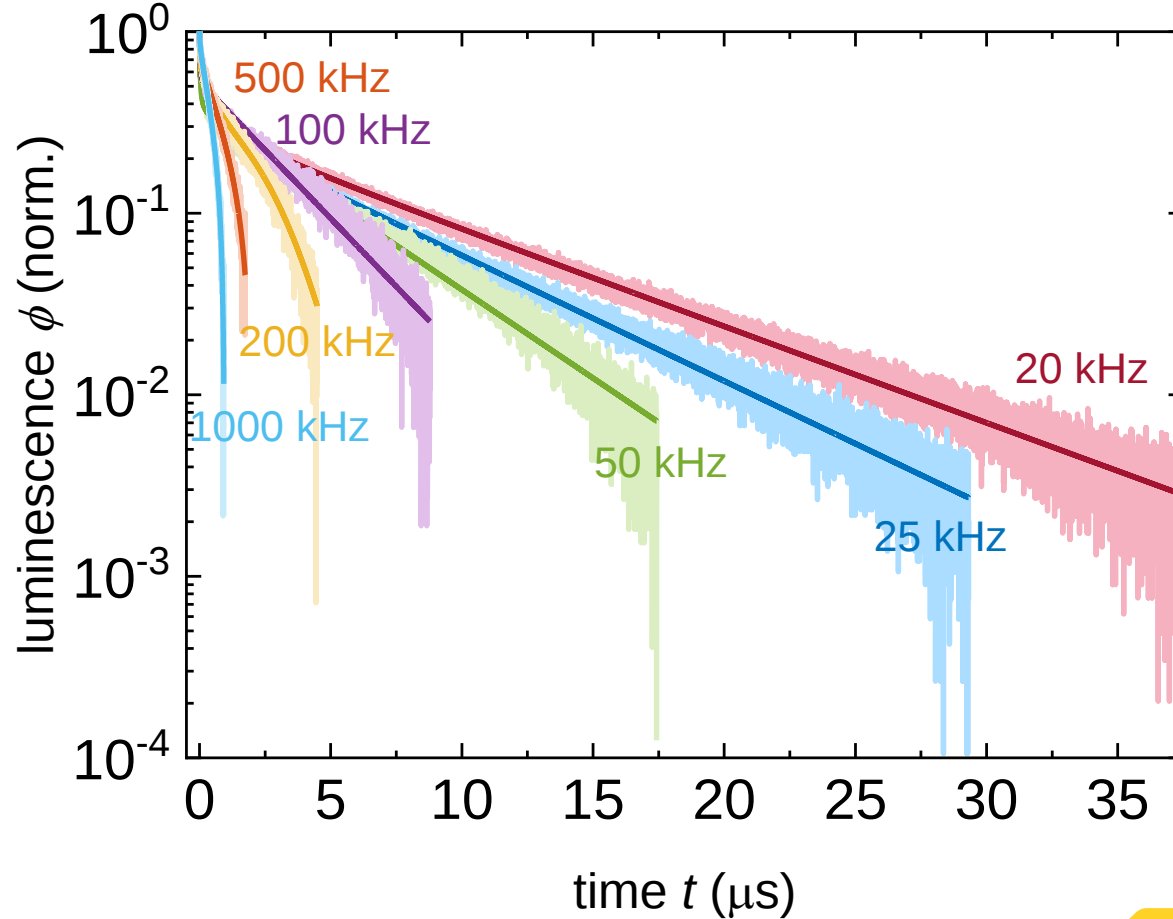


Shallow defects lead to non-integer n_{id} and continuously increasing decay times. High defect density needed to fit the data.

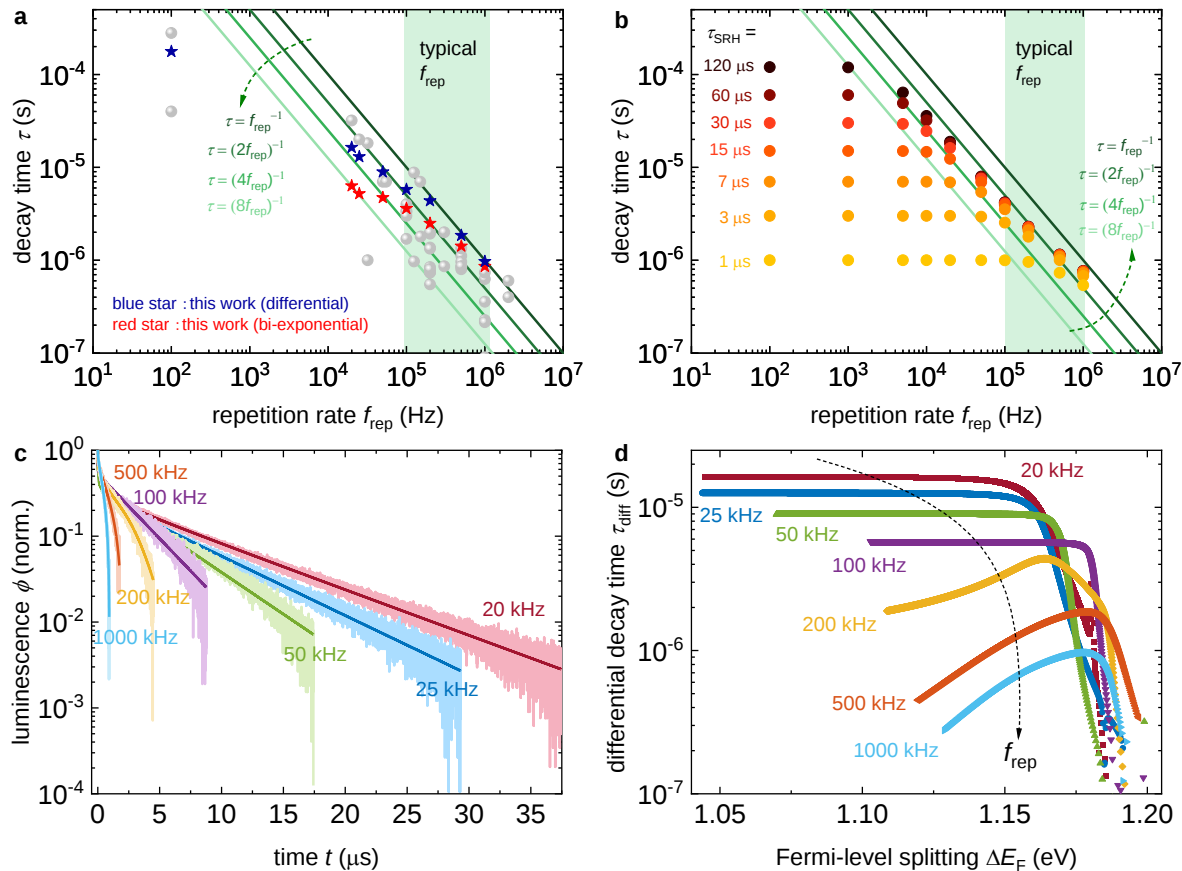


PART 2: REPETITION RATES AND HOW THEY AFFECT DECAY TIMES

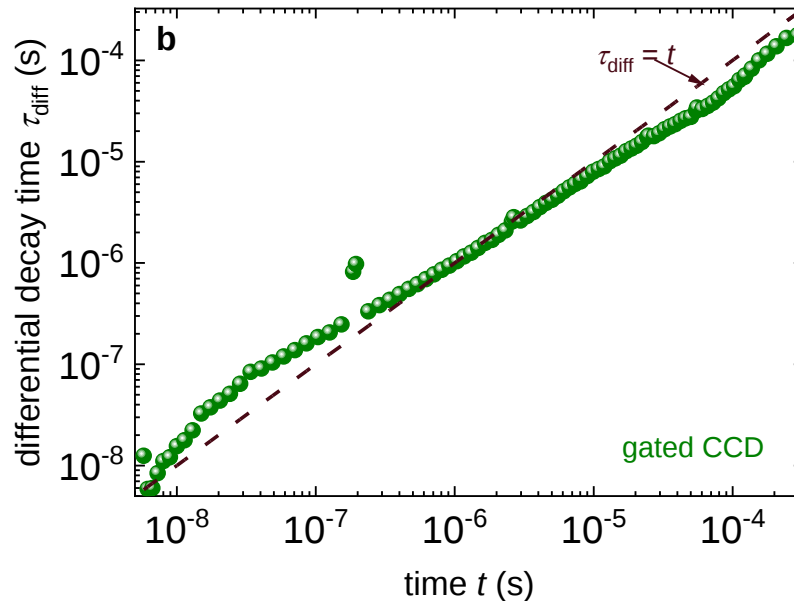
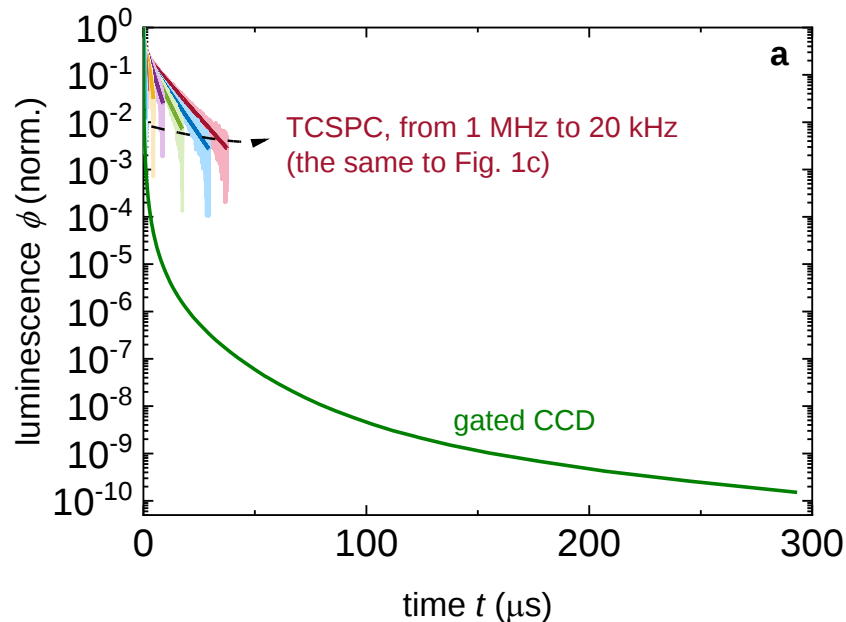
Decays vs. repetition rates



Decays vs. repetition rates



Why $\tau = t$ can be a decent approximation

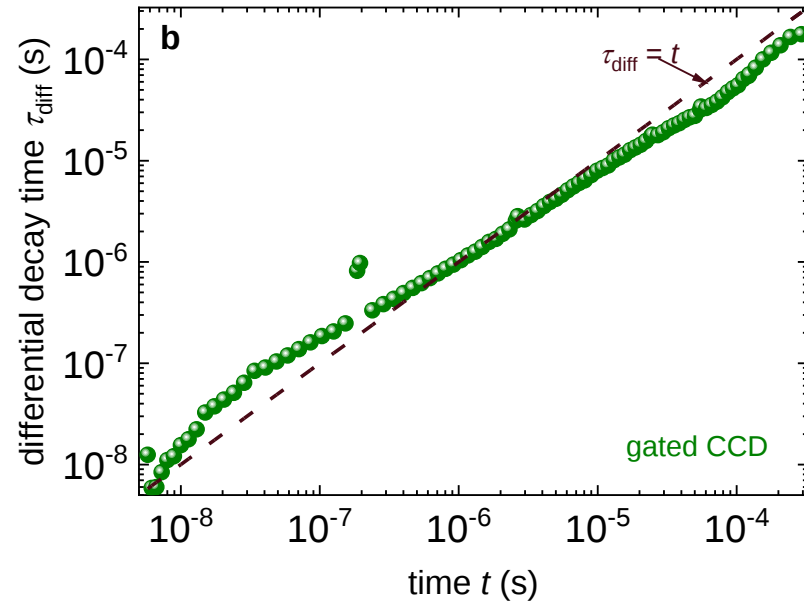
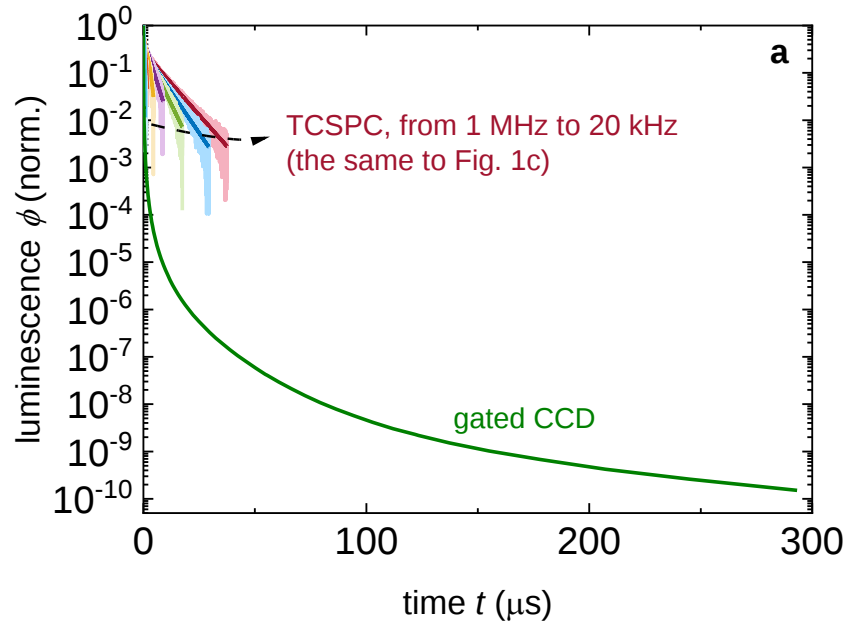


$$\frac{dn(t)}{dt} = -kn^2$$

$$\tau_{\text{diff}} = (kn(t))^{-1}$$

$$n(t) = \frac{n(0)}{1 + n(0)kt} \approx 1/(kt)$$

Why $\tau = t$ can be a decent approximation



$$\frac{dn(t)}{dt} = -kn^2$$

$$\tau_{\text{diff}} = (kn(t))^{-1}$$

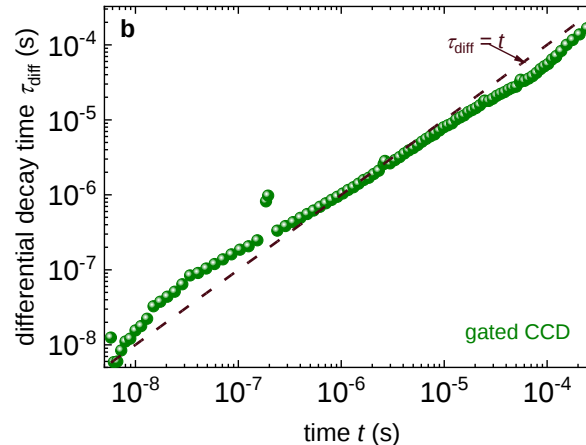
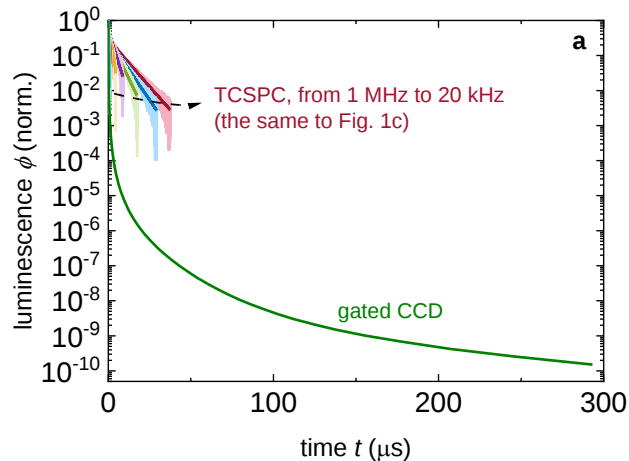
$$n(t) = \frac{n(0)}{1 + n(0)kt} \approx 1/(kt)$$

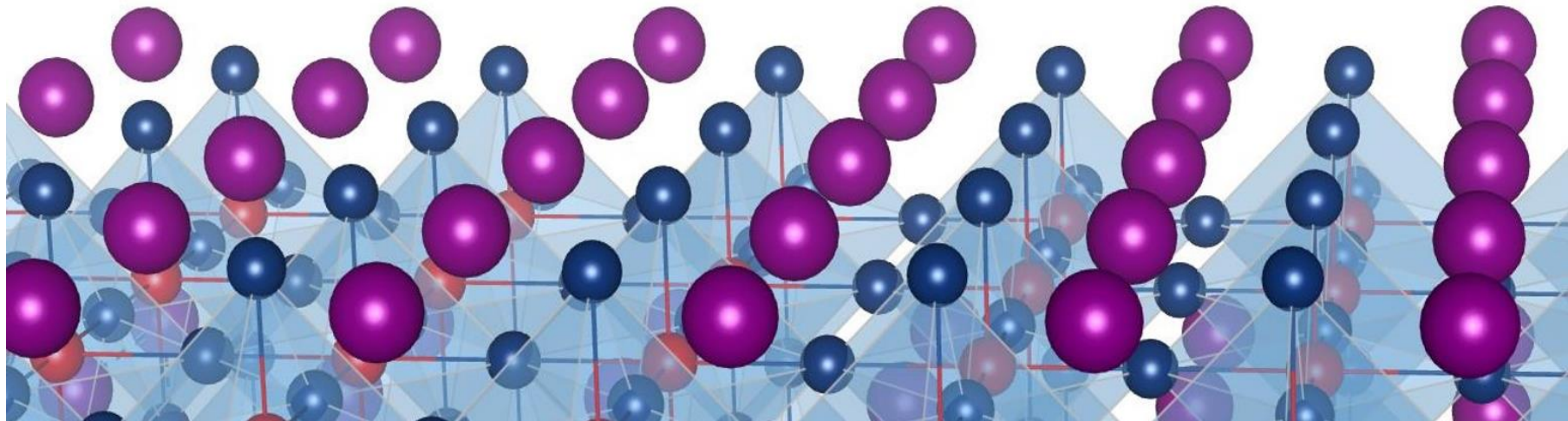
$$\tau_{\text{diff}} = t$$

Summary

If a sample is intrinsic, the following holds:

- Every decay not dominated by a deep defect will lead to non-exponential decays.
- Those are often similar to radiative recombination (even if they are not)
- They will automatically lead to $\tau_{\text{diff}} \approx t$ implying that decay times determined towards the end of a decay are $\sim$ the inverse repetition rate.

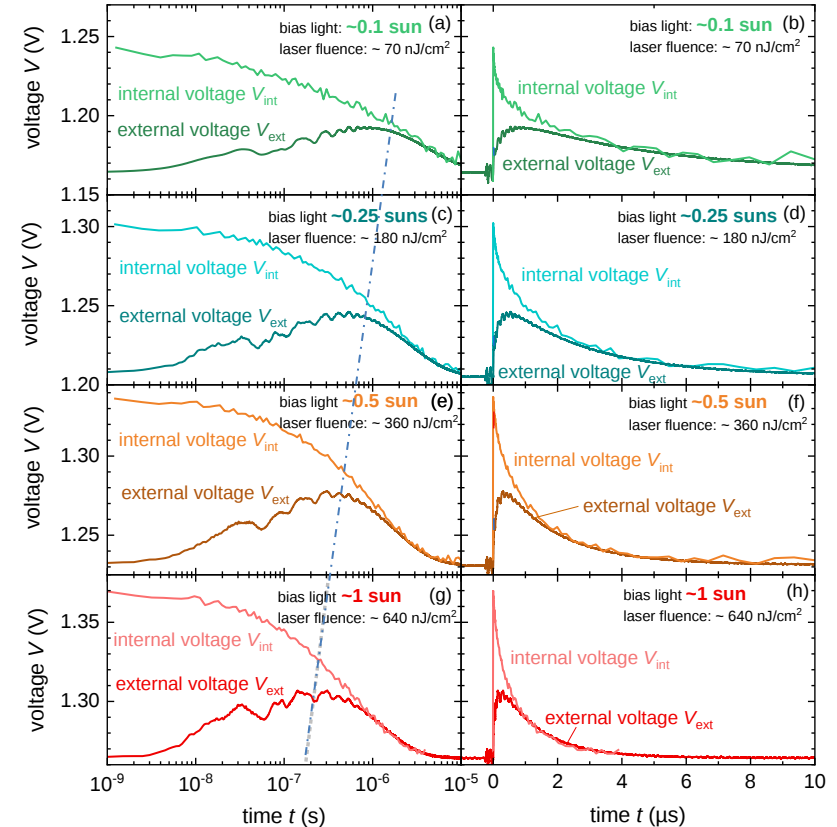
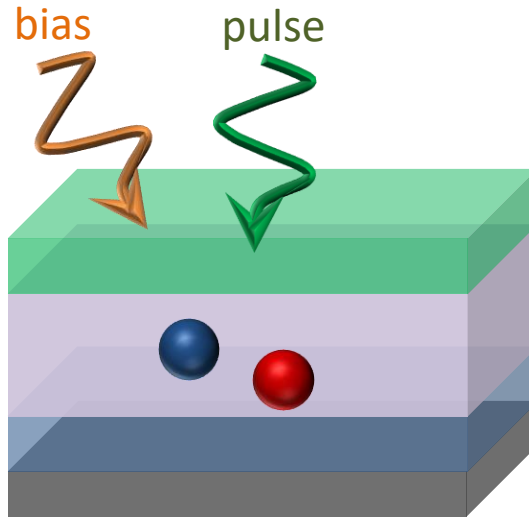




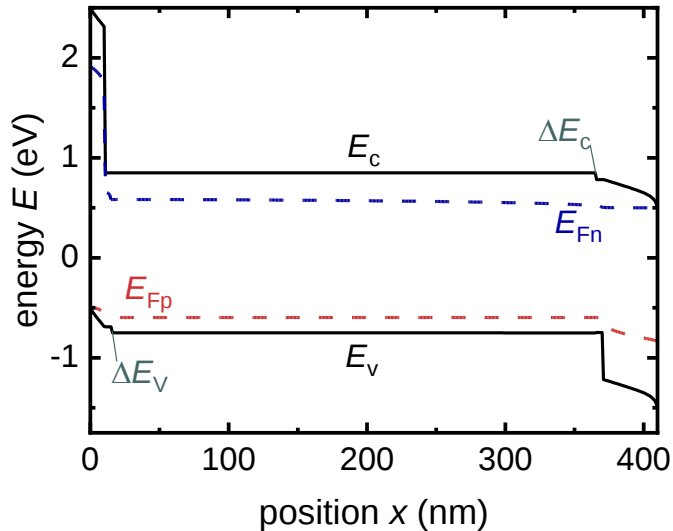
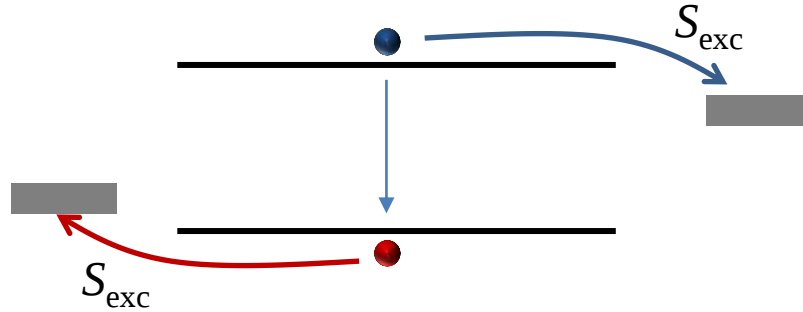
PART 3: ANALYSIS OF SMALL SIGNAL MEASUREMENTS

EIGENVALUES OF MATRICES ☺

Experimental data – internal vs. external voltage



Transient Methods – Recombination and Extraction



$$\frac{dn}{dt} = -k_{\text{rad}} n^2 - \frac{n}{\tau_{\text{SRH}}^{\text{eff}}} - \frac{S_{\text{exc}}}{d} \left(n - n_i \exp\left(\frac{qV_{\text{ext}}}{2kT}\right) \right) + G$$

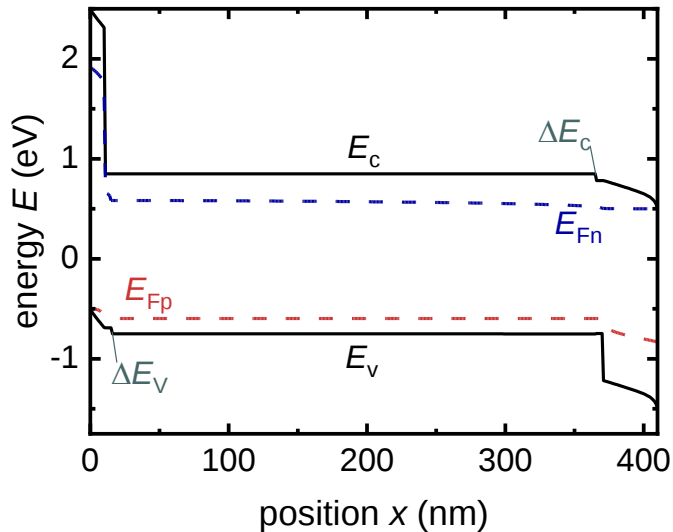
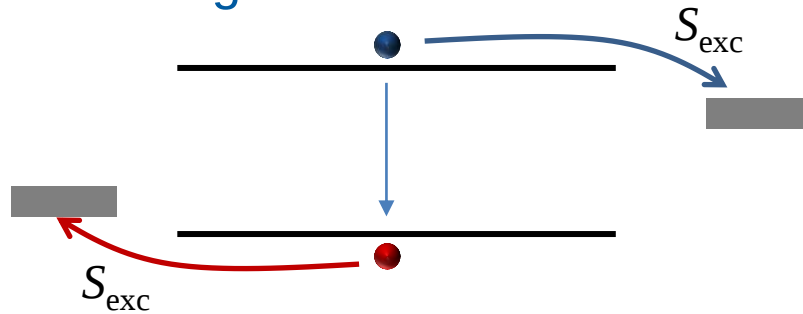
Recombination and extraction

$$\frac{dV_{\text{ext}}}{dt} = \frac{qS_{\text{exc}}}{C_{\text{area}}} \left(n - n_i \exp\left(\frac{qV_{\text{ext}}}{2kT}\right) \right)$$

Electrode (dis)charging

Recombination and Extraction

Small signal solution



$$\frac{d}{dt} \begin{pmatrix} \delta V_{\text{int}} \\ \delta V_{\text{ext}} \end{pmatrix} = \begin{pmatrix} -\left(\frac{1}{\tau_{\text{SRH}}^{\text{eff}}} + 2k_{\text{rad}} n_{\text{bias}} + \frac{S_{\text{exc}}}{d} \right) & \frac{S_{\text{exc}}}{d} \\ \frac{S_{\text{exc}} n_{\text{bias}}}{dn_Q} & -\frac{S_{\text{exc}} n_{\text{bias}}}{dn_Q} \end{pmatrix} \begin{pmatrix} \delta V_{\text{int}} \\ \delta V_{\text{ext}} \end{pmatrix}$$

$$\tau_{\text{rise}} = \frac{2}{k_1 + k_2 + k_3 + \sqrt{(k_1 + k_2 + k_3)^2 - 4k_1 k_3}}$$

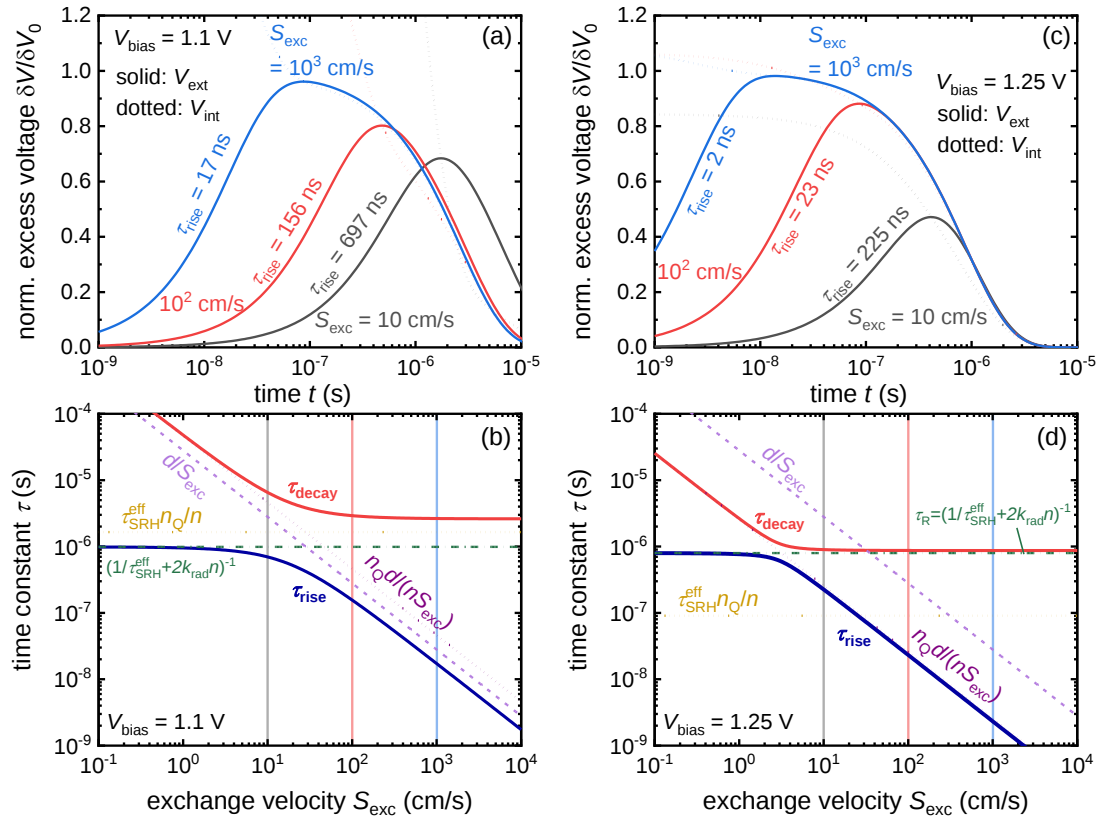
$$\tau_{\text{decay}} = \frac{2}{k_1 + k_2 + k_3 - \sqrt{(k_1 + k_2 + k_3)^2 - 4k_1 k_3}}$$

$$k_1 = \frac{1}{\tau_{\text{SRH}}^{\text{eff}}} + 2k_{\text{rad}} n_{\text{bias}}, \quad k_2 = \frac{S_{\text{exc}}}{d}, \quad k_3 = \frac{S_{\text{exc}} n_{\text{bias}}}{dn_Q}$$

Inverse Eigenvalues of Matrix

Recombination and Extraction

Variation of S_{exc}



$$\frac{d}{dt} \begin{pmatrix} \delta V_{\text{int}} \\ \delta V_{\text{ext}} \end{pmatrix} = \begin{pmatrix} -\left(\frac{1}{\tau_{\text{SRH}}^{\text{eff}}} + 2k_{\text{rad}} n_{\text{bias}} + \frac{S_{\text{exc}}}{d} \right) & \frac{S_{\text{exc}}}{d} \\ \frac{S_{\text{exc}} n_{\text{bias}}}{dn_Q} & -\frac{S_{\text{exc}} n_{\text{bias}}}{dn_Q} \end{pmatrix} \begin{pmatrix} \delta V_{\text{int}} \\ \delta V_{\text{ext}} \end{pmatrix}$$

$$\tau_{\text{rise}} = \frac{2}{k_1 + k_2 + k_3 + \sqrt{(k_1 + k_2 + k_3)^2 - 4k_1 k_3}}$$

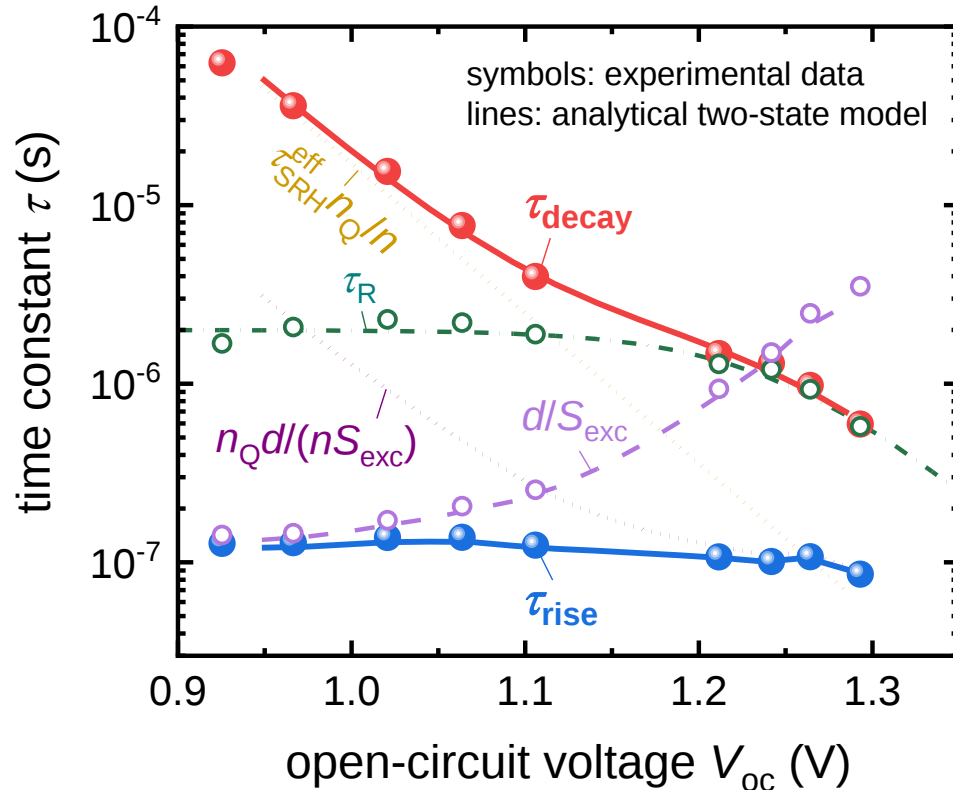
$$\tau_{\text{decay}} = \frac{2}{k_1 + k_2 + k_3 - \sqrt{(k_1 + k_2 + k_3)^2 - 4k_1 k_3}}$$

$$k_1 = \frac{1}{\tau_{\text{SRH}}^{\text{eff}}} + 2k_{\text{rad}} n_{\text{bias}}, \quad k_2 = \frac{S_{\text{exc}}}{d}, \quad k_3 = \frac{S_{\text{exc}} n_{\text{bias}}}{dn_Q}$$

Inverse Eigenvalues of Matrix

Recombination and Extraction

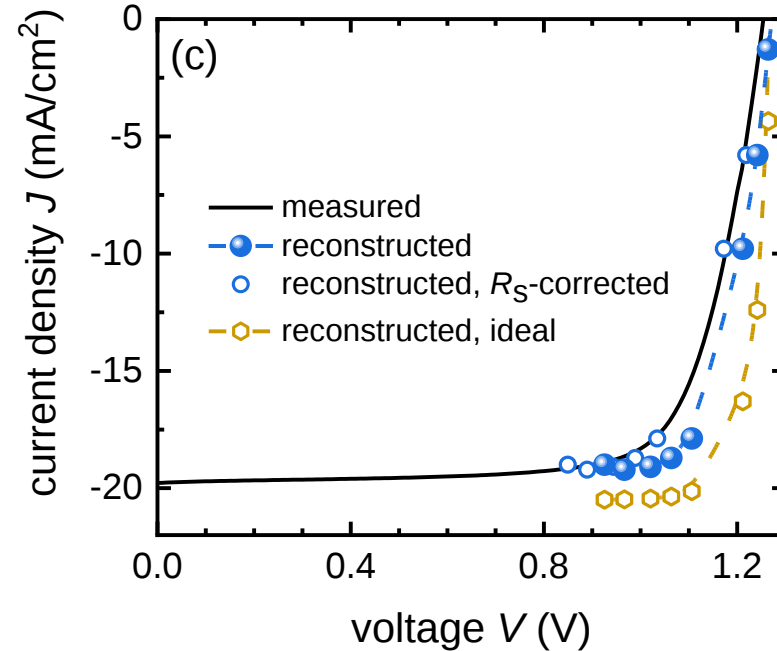
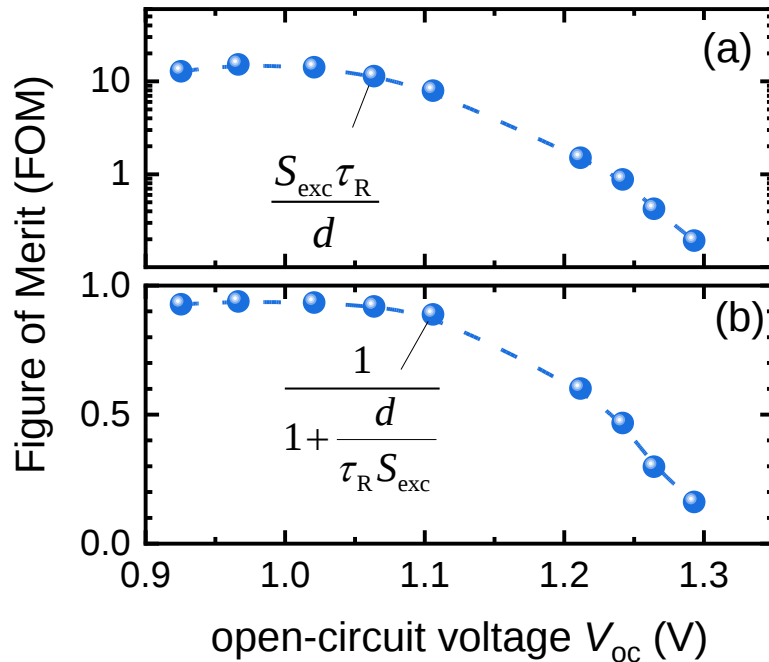
Comparison with Experiment



$$\tau_{\text{decay}} \approx \frac{dn_Q}{S_{\text{exc}} n_{\text{bias}}} + \frac{\tau_R n_Q}{n_{\text{bias}}} + \tau_R$$

$$\tau_{\text{rise}} \approx \left(\frac{1}{\tau_R} + \frac{S_{\text{exc}}}{d} + \frac{S_{\text{exc}} n_{\text{bias}}}{dn_Q} \right)^{-1}$$

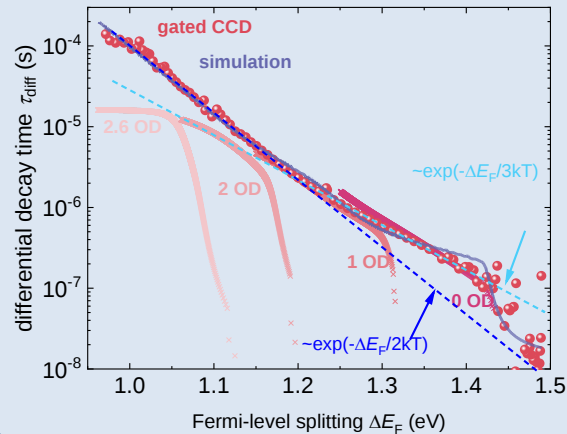
Collection Efficiencies and Impact on JV curves



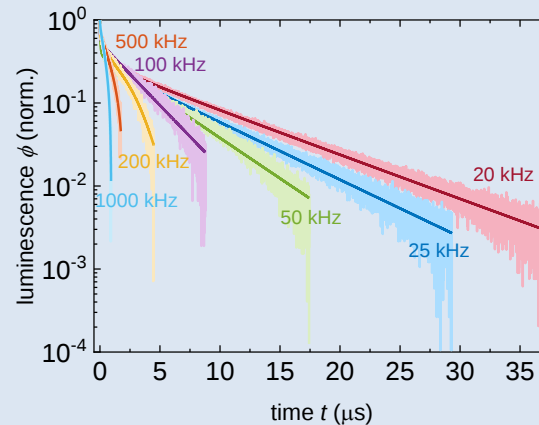
$$J = qd(R - G) = qd \left(\frac{1}{1 + d/(S_{\text{exc}} \tau_R)} \right) \left[\frac{n_0}{\tau_R} \exp \left(\frac{qV_{\text{ext}}}{2k_B T} \right) - G \right]$$

Summary

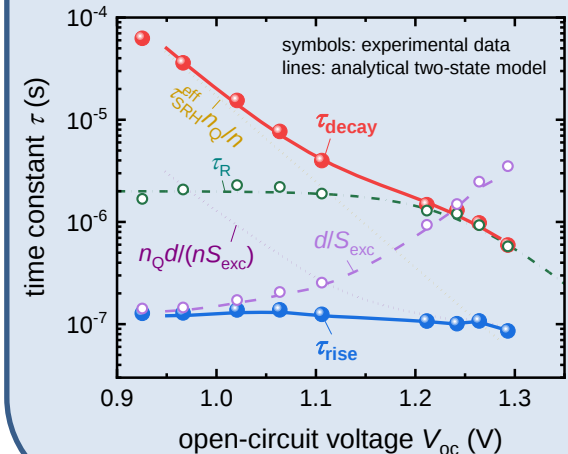
1) Decay time can continuously increase for shallow defect rec.



2) $\tau \sim 1/f_{rep}$ is a risk to consider.



3) Small signal solvable via eigenvalues of matrix
→ information on extraction & recomb.





Funding from
Helmholtz Association
DFG
OCPC Fellowships

Thank you for your attention